FIG.1

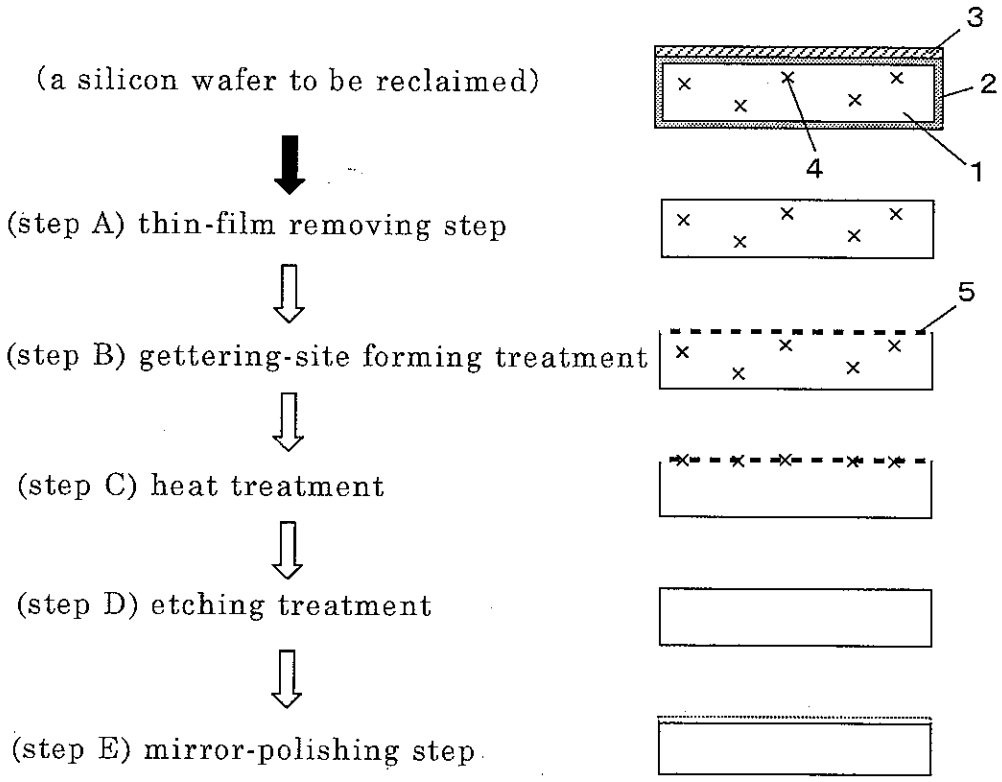

(a silicon wafer to be reclaimed)
(step A) thin-film removing step
(step B) gettering-site forming treatment
(step C) heat treatment
(step D) etching treatment
(step E) mirror-polishing step
3
2
4
1
5

FIG.2

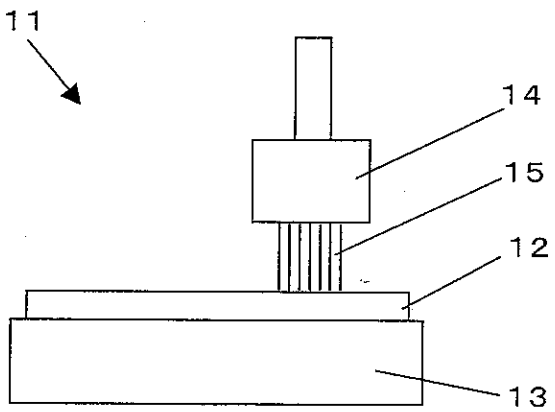

11
14
15
12
13

FIG. 3

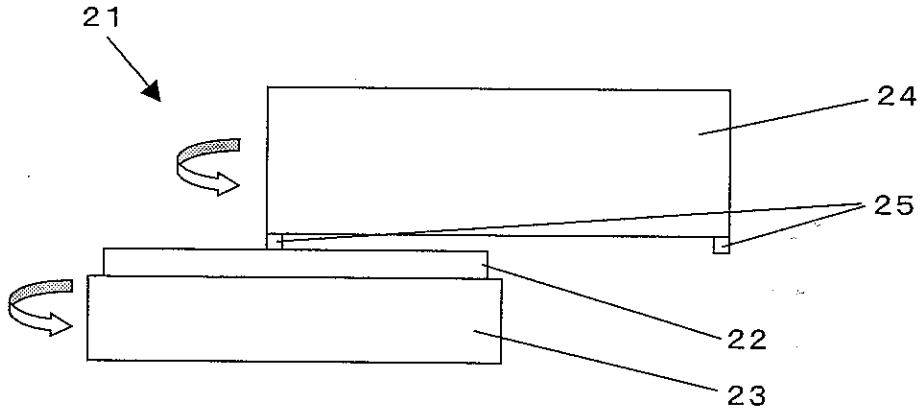
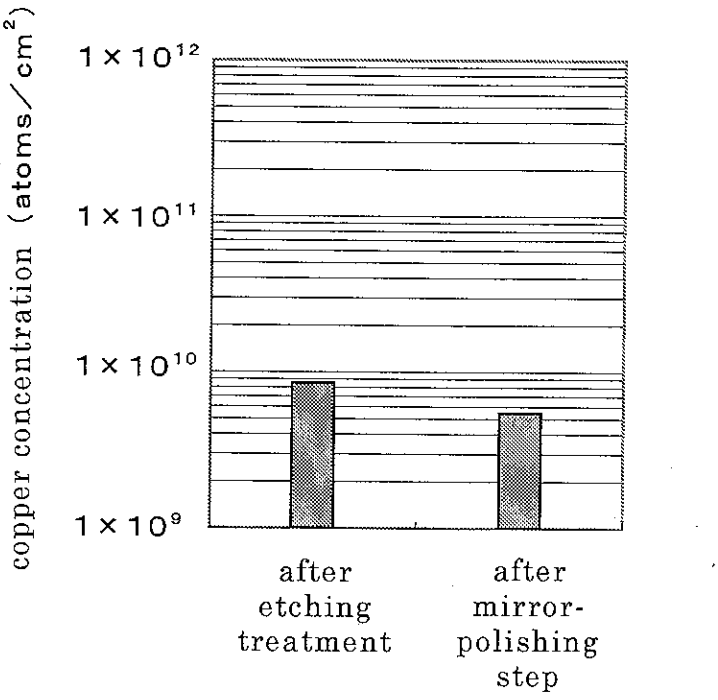

21
24
25
22
23

FIG. 4


copper concentration (atoms/cm²)
1×10¹²
1×10¹¹
1×10¹⁰
1×10⁹
after etching treatment
after mirror-polishing step